



DATA SHEET

MMBT3906

PNP GENERAL PURPOSE TRANSISTORS

VOLTAGE -40 V CURRENT -200 mA

FEATURES

- HIGH DC CURRENT GAIN
- LOW COLLECTOR-EMITTER SATURATION VOLTAGE
- LEAD FREE AND HALOGEN-FREE

MECHANICAL DATA

- CASE: SOT-23
- TERMINALS: SOLDERABLE PER MIL-STD-202, METHOD 208
- APPROX. WEIGHT: 0.008 GRAMS





CASE: SOT-23

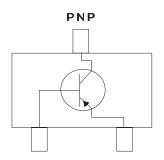
ABSOLUTE MAXIMUM RATINGS

AT T_A=25°C, UNLESS OTHERWISE SPECIFIED.

PARAMETER	SYMBOL	VALUE	UNITS
COLLECTOR-EMITTER VOLTAGE	V_{CEO}	-40	V
COLLECTOR-BASE VOLTAGE	V_{CBO}	-40	V
EMITTER-BASE VOLTAGE	$V_{\rm EBO}$	-5	V
COLLECTOR CURRENT-CONTINUOUS	I_{C}	-200	mA
POWER DISSIPATION	P_{D}	225	mW
THERMAIL RESISTANCE, JUNCTION TO AMBIENT	$R_{\theta JA}$	417	°C/W
JUNCTION TEMPERATURE	T_{J}	150	°C
TORAGE TEMPERATURE RANGE	T_{STG}	-55 to +150	°C

NOTE:

1. ABSOLUTE MAXIMUM RATINGS ARE THOSE VALUES BEYOND WHICH THE DEVICE COULD BE PERMANENTLY DAMAGED. ABSOLUTE MAXIMUM RATINGS ARE STRESS RATINGS ONLY AND FUNCTIONAL DEVICE OPERATION IS NOT IMPLIED.







ELECTRICAL CHARACTERISTICS

AT T_A= 25°C, UNLESS OTHERWISE NOTED

11					
OFF CHARACTERISTICS					
PARAMETER	TEST CONDITION	SYMBOL	MIN.	MAX.	UNITS
COLLECTOR-EMITTER BREAKDOWN VOLTAGE	$I_{\rm C} = -1 \text{mA}, I_{\rm B} = 0$	V _{(BR)CEO}	-40	-	V
COLLECTOR-BASE BREAKDOWN VOLTAGE	$I_{\rm C} = -10 \mu A, I_{\rm E} = 0$	$V_{(BR)CBO}$	-40	-	V
EMITTER-BASE BREAKDOWN VOLTAGE	$I_E = -10 \mu A, I_C = 0$	$V_{(BR)EBO}$	-5	-	V
EMITTER CUT-OFF CURRENT	$V_{EB} = -3V$, $I_C = 0$	I_{EBO}	-	-50	nA
COLLECTOR CUT-OFF CURRENT	$V_{CE} = -30V$, $V_{EB} = -3V$	I_{CEX}	-	-50	nA
ON CHARACTERISTICS					
	$I_C = -0.1 \text{mA}, V_{CE} = -1 \text{V}$		60	-	-
DC CURRENT GAIN	$I_{\rm C} = -1 \text{mA}, V_{\rm CE} = -1 \text{V}$		80	-	
	$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$	h_{FE}	100	300	
	$I_C = -50 \text{mA}, V_{CE} = -1 \text{V}$		60	-	
	$I_C = -100 \text{mA}, V_{CE} = -1 \text{V}$		30	-	
COLLECTOR EMITTER CATURATION VOLTACE	$I_{C} = -10 \text{mA}, I_{B} = -1 \text{mA}$	V	-	-0.25	V
COLLECTOR-EMITTER SATURATION VOLTAGE	$I_{C} = -50 \text{mA}, I_{B} = -5 \text{mA}$	V _{CE(SAT)}	-	-0.4	
SE-EMITTER SATURATION VOLTAGE $I_C = -10mA, I_B = -1mA$ V	V	-	-0.85	V	
BASE-EMITTER SATURATION VOLTAGE	$I_{C} = -50 \text{mA}, I_{B} = -5 \text{mA}$	$V_{BE(SAT)}$	-	-0.95	7 v
SMALL-SIGNAL CHARACTERISTICS					
COLLECTOR OUTPUT CAPACITANCE	$V_{CB} = -5V, I_E = 0, f = 1MHz$	Cob	-	4.5	pF
CURRENT-GAIN-BANDWIDTH PRODUCT	$I_{C} = -10 \text{mA}, V_{CE} = -20 \text{V},$ f = 100 MHz	f_T	250	-	MHz

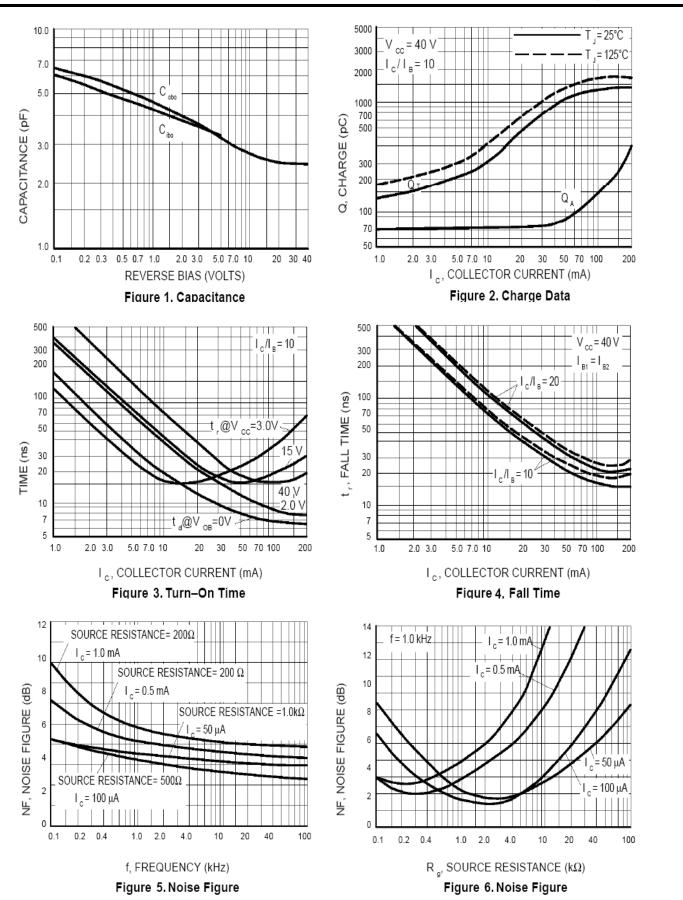
NOTE:

1. PULSE TEST: PULSE WIDTH $\leq 300 \mu s$; DUTY CYCLE $\leq 2\%$.

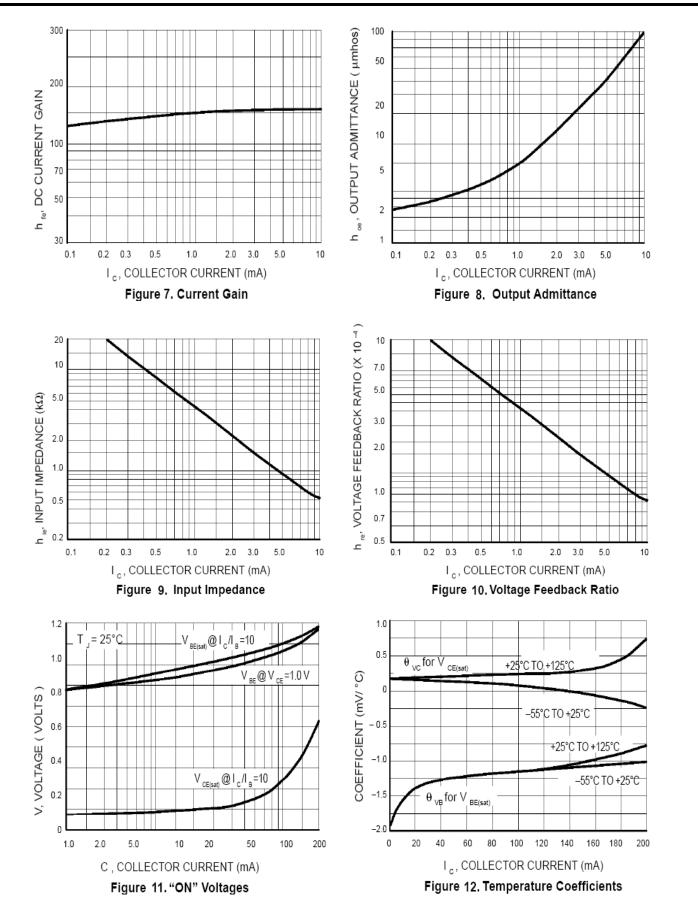
ORDERING INFORMATION

PART NUMBER	PACKAGE	SHIPPING	
MMBT3906-T3R	SOT-23	TAPE REEL	



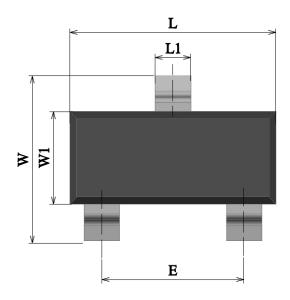


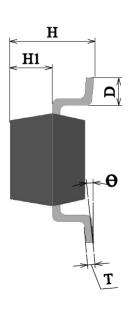






SOT-23 DIMENSION





Symbol	Dimensions I	nensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max		
L	2.80	3.10	0.110	0.122		
L1	0.30	0.50	0.012	0.020		
W	2.25	2.54	0.089	0.100		
W1	1.20	1.40	0.047	0.055		
Е	1.80	2.00	0.071	0.079		
Н	0.90	1.15	0.035	0.045		
H1	0.40	0.80	0.016	0.031		
D	0.30	0.50	0.012	0.020		
T	0.08	0.15	0.003	0.006		
θ	0°	8°	0 °	8°		

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